查询"23%497"共应商OSHIBA (DISCRETE/OPTO)

56C 08007

T-39-11

SILICON N CHANNEL MOS TYPE (π-MOS)

2SK420

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS. SWITCHING REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS.

FEATURES:

- . High Breakdown Voltage : V(BR)DSS=400V
- . High Forward Transfer Admittance : $|Y_{fs}| = 2.5S$ (Typ.)
- . Low Leakage Current : IGSS= ± 100 nA(Max.) @ VGS= ± 20 V

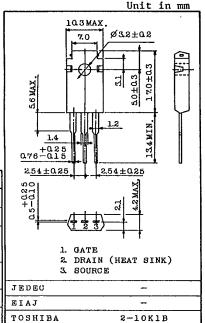
IDSS=1mA(Max.) @ VDS=400V

. Enhancement-Mode : $V_{th}=1.5\sim3.5V$ @ $I_D=1mA$

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTI	C	SYMBOL	RATING	UNIT	
Drain-Source Voltage		V _{DSX}	400	v	
Gate-Source Voltage		VGSS	±20	V	
Drain Current	DC	I _D 5		A	
Drain Garrene	Pulse	IDP	8	^	
Drain Power Dissipati (Tc=25°C)	PD	60	W		
Channel Temperature		Tch	150	°C	
Storage Temperature Range		Tstg	-55~150	°C	

INDUSTRIAL APPLICATIONS



Weight: 2.0g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	V _{GS} =±20V, V _{DS} =0	-	-	±100	nA
Drain Cut-off Current		· IDSS	VDS=400V, VGS=0	-	-	1.0	mA
Drain-Source Breakdown Voltage		V(BR)DSS	ID=10mA, VGS=0	400	-	-	V
Gate Threshold Voltage		V _{th}	VDS=10V, ID=1mA	1.5	-	3.5	V
Forward Transfer Admittance		lYfsl	V _{DS} =10V, I _D =3A	1.0	2.5	_	S
Drain-Source ON Resistance		RDS (ON)	I _D =3A, V _{GS} =10V	-	1.0	1.4	Ω
Drain-Source ON Voltage		V _{DS} (ON)	ID=8A, VGS=10V	-	10	18	V
Input Capacitance		Ciss	VDS=10V, VGS=0, f=1MHz	-	670	900	рF
Reverse Transfer Capacitance		Crss	VDS=10V, VGS=0, f=1MHz	_	50	90	рF
Output Capacitance		Coss	V _{DS} =10V, V _{GS} =0, f=1MHz	_	180	250	рF
Switching Time	Rise Time	tr	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	25	50	ns
	Turn-on Time	ton		-	40	80	กร
	Fall Time	tf		-	35	70	ns
	Turn-off Time	toff		-	140	280	ns

THIS TRANSISTOR IS THE ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

INCOMPOSITION OF THE PROPERTY OF THE PROPERTY